

優恩半導體 UN Semiconductor[®]



Transient Voltage Suppressors for ESD Protection

LC2504-P9

Description

Feature

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The LC2504P9 is ultra low capacitance TVS arrays designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from over-voltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

1000Watts Peak Pulse Power per Line (tp=8/20µs)



Functional Diagram

- Protects Two I/O Lines (Pairs)
- Low Clamping Voltage
- Working voltages : 2.5V
- ♦ IEC61000-4-2(ESD):±30kV (air discharge) ±30kV (contact discharge);
- IEC61000-4-4 (EFT) 40A (5/50 η s)
- IEC61000-4-5 (LIGHTING) 50A (8/20 μ s)



Applications

- ◆ 10/100/1000 Ethernet
- Central Office Equipment
- LVDS Interfaces
- MagJacks / Integrated Magnetics
- Notebooks / Desktops / Servers
- ATM Interfaces

Mechanical Data

- DFN2626P9 (2.6x2.6x0.5mm) Package
- Molding Compound Flammability Rating : UL 94V-O
- Weight 12 Millgrams (Approximate)
- Quantity Per Reel : 3,000pcs
- Reel Size : 7 inch
- Lead Finish : Lead Free
- Device Marking: LC2504P9

Mechanical Characteristics

Symbol	Parameter	Value	Units
Ррр	Peak Pulse Power (tp=8/20µs waveform)	1000	Watts
TJ	Operating Junction Temperature Range	-40 to +125	°C
Т _{stg}	Storage Temperature Range	-55 to +150	°C
T∟	Soldering Temperature, T max = 10s	260	°C

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Electrical Characteristics (@ 25°C Unless Otherwise Specified)

Part Number	Device Marking Code		Stand-Off Voltage V _{RMW} (V)	Breakdown Voltage V _{BR}	Test Current IT (mA)	V c @5A (Max.)	V c		Maximum Reverse	Maximum Junction
							(Max.)	(@A)	Leakage I _R @V _{RWM} (uA)	Capacitance @0 V (pF)
LC2504-P9	LC2504-P9	I/O to I/O	2.5	3.0	1.0	8.0	21	30	0.05	1.3
		Line to Line	2.5	3.0	1.0	6.0	25	40	0.05	2.6

Characteristic Curves

Fig1. Power Derating Curve



Fig3. Clamping Voltage vs. Peak Pulse Current (tp=8/20us)



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Fig2. 8/20us Pulse Waveform



Fig4. Typic Capacitance vs. Reverse Voltage



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DFN2626P9 Package Outline & Dimensions









Symbol	Dimensions In Millimeters		Dimensions In Inches		
	MIN.	MAX.	MIN.	MAX.	
А	0.500	0.600	0.020	0.024	
A1	-0.004	0.046	0.000	0.002	
A3	0.110REF.		0.004	4REF.	
D	2.500	2.700	0.098	0.106	
E	2.500	2.700	0.098	0.106	
b	0.200	0.300	0.008	0.012	
е	0.500BSC.		0.020BSC.		
e1	1.000BSC.		0.039BSC.		
k	1.750REF.		0.069REF.		
L	0.274	0.426	0.011	0.017	
L1	0.075REF.		0.003REF.		

*** SOLDERING FOOTPRINT**



DIMENSIONS			
C	2.30		
G	1.70		
Р	0.50		
X	0.30		
Y	0.60		
Z	2.95		

DIMENSIONS : MILLIMETERS

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APPLICATION INFORMATION



Line to Line Schematic Diagram for Gigabit Ethernet Telcordia GR-1089 Intra-Building Protection (PHY Operating Temp <= 90°C)

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